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# **Dual P-Channel 30-V (D-S) MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
- 30	0.031 at V <sub>GS</sub> = - 10 V	- 4.7		
	0.048 at V <sub>GS</sub> = - 4.5 V	- 3.8		

#### **FEATURES**

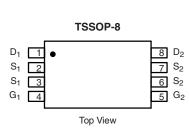
- · Halogen-free
- TrenchFET® Power MOSFETs



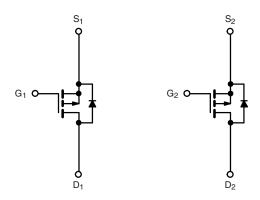
RoHS

#### **APPLICATIONS**

- · Load Switch
- · Battery Switch



Ordering Information: Si6993DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 30		V	
Gate-Source Voltage		V <sub>GS</sub>	± 20			
Continuous Dunin Courset /T 150 °C\2	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 4.7	- 3.6		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 3.8	- 3.2	Δ.	
Pulsed Drain Current (10 µs Pulse Width)		I <sub>DM</sub>	- 30		Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 1.0	- 0.70		
Martineau Branco Biochartina	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	1.14	0.83	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		0.73	0.53		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestore baseding to Applicated	t ≤ 10 s	- R <sub>thJA</sub>	86	110	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		124	150		
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	52	65		

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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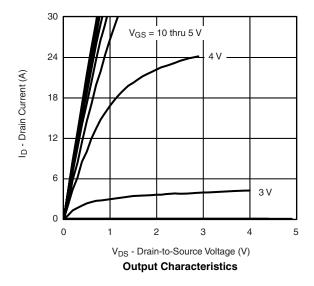
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit	
Static				1	<u>I</u>		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Cata Valtana Busin Comunit	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α	
Drain-Source On-State Resistance <sup>a</sup>	D	$V_{GS} = -10 \text{ V}, I_D = -4.7 \text{ A}$		0.024	0.031	0	
	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -3.8 \text{ A}$		0.038	0.048	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 4.7 A		14		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 1.0 A, V <sub>GS</sub> = 0 V		- 0.74	- 1.1	V	
Dynamic <sup>b</sup>				•			
Total Gate Charge	$Q_g$			13	20		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		3		nC	
Gate-Drain Charge	$Q_{gd}$			5.8			
Gate Resistance	$R_g$	f = 1.0 MHz		4.6		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			13	20		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		14	22		
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong$ - 1 A, $\text{V}_\text{GEN}$ = - 10 V, $\text{R}_\text{G}$ = 6 $\Omega$		52	80	ns	
Fall Time	t <sub>f</sub>			26	40		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.0 A, dl/dt = 100 A/μs		40	60		

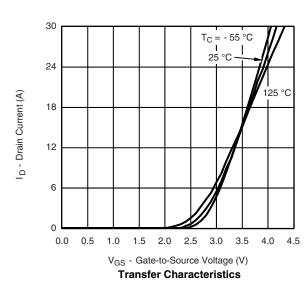
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

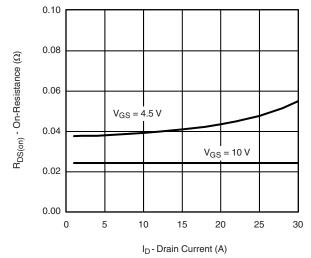
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



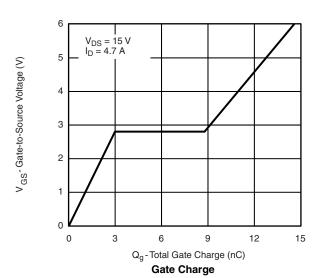




#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



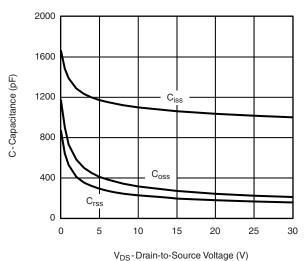
On-Resistance vs. Drain Current



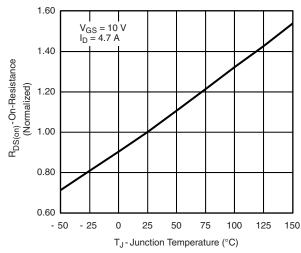
Is - Source Current (A)  $T_J = 25 \, ^{\circ}C$ 0.1 0.0 0.3 0.9 1.2 1.5

T<sub>J</sub> = 150 °C

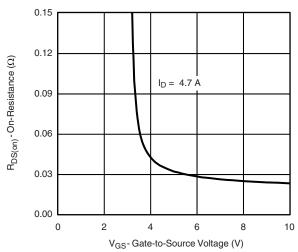
V<sub>SD</sub>-Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage







On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

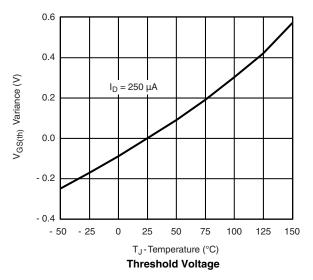
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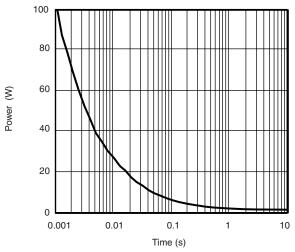
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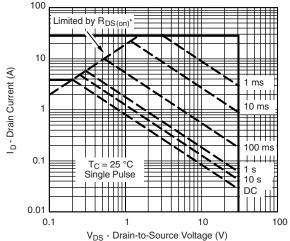
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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

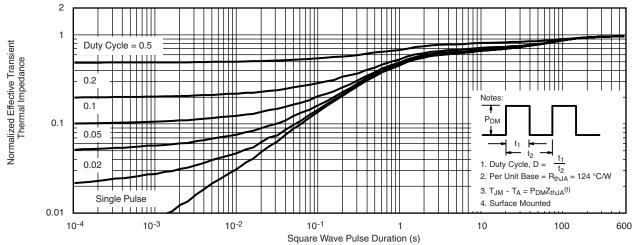




Single Pulse Power, Junction-to-Ambient



 $^{\star}$  V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified **Safe Operating Area, Junction-to-Case** 



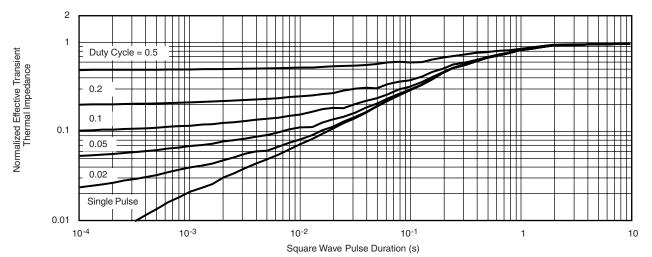
Normalized Thermal Transient Impedance, Junction-to-Ambient







#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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